

OA1182
Gold Bonded Germanium Diode

FEATURES

- Low forward voltage drop—low power consumption
- Thirty years of proven reliability—one million hours mean time between failures (MTBF)
- Very low noise level
- Metallurgically bonded

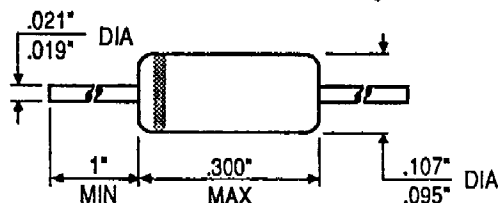
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage	100 Volts
Peak Forward Current	500 mA
Operating Temperature	- 65 °C to 85 °C
Average Power Dissipation	80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	100		V	25 °C
Reverse Current	I_r	60 V		20	μ A	25 °C
Forward Voltage	V_f	100 mA		0.85	V	25 °C

MECHANICAL



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

